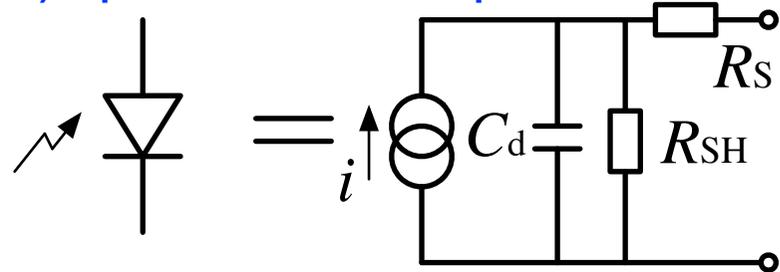


## A) Equivalent circuit for a photodiode



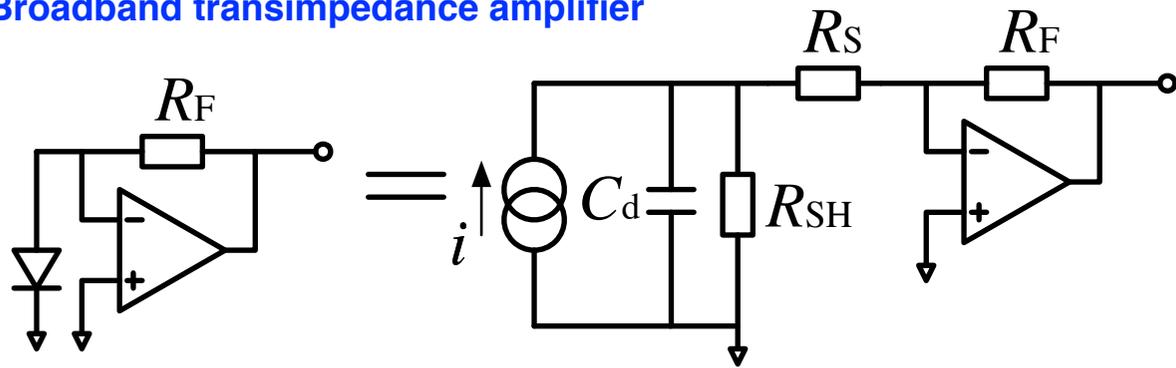
$$R_{SH} = 4 k T / i_{\text{dark}}^2$$

$$\sim 100 \text{M Ohm for } 1.3 \times 10^{-14} \text{ A/Hz}^{1/2}$$

$$R_S \sim 10 \text{ Ohm}$$

$$C_d \sim 100 \text{ pF}$$

## B) Broadband transimpedance amplifier



$$V_{\text{shot}} = i_{\text{shot}} R_F = R_F \text{ sqrt}(2 e i_{\text{dc}})$$

$$V_{\text{th,RSH}} = R_F \text{ sqrt}(4 k T / R_{SH})$$

$$V_{\text{th,RF}} = \text{sqrt}(4 k T R_F) (\gg V_{\text{th,RSH}})$$

$$V_{\text{th,RS}} \sim R_F \text{ sqrt}(4 k T R_S) / R_{SH} * (1 + i f / f_{SH}) / (1 + i f / f_S)$$

$$(f_{SH} = 1 / (2 \text{ pi } R_{SH} C_d), f_S = 1 / (2 \text{ pi } R_S C_d))$$

$$V_{\text{th,RS}@f=0} = R_F \text{ sqrt}(4 k T R_S) / R_{SH}$$

$$V_{\text{th,RS}@f=\text{High}} = R_F \text{ sqrt}(4 k T / R_S)$$

$$V_{\text{shot}} = R_F \sqrt{2 e i_{\text{dc}}}$$

### Low freq regime

Amplifier noise is dominant (unless  $R_{\text{SH}} \sim R_F$ )

$$V_{\text{th}} \sim \sqrt{4 k T R_F}$$

$V_{\text{shot}} = V_{\text{th}}$  when

$$i_{\text{dc}} = 2 k T / (e R_F)$$

e.g.  $i_{\text{dc}} = 0.05 \text{ mA}$  for  $R_F = 1000 \text{ Ohm} \implies (V_{\text{th}} = 4 \text{ nV/Hz}^{1/2})$

### High freq regime

Noise of  $R_s$  is dominant

(i.e. current noise of  $R_s$ , or voltage noise of  $R_s$  amplified by  $R_F/R_s$ )

$R_{\text{SH}}$  can be ignored

$$V_{\text{th}} \sim R_F \sqrt{4 k T / R_s} |(i f / f_s) / (1 + i f / f_s)|$$

$V_{\text{shot}} = V_{\text{th}}$  when

$$i_{\text{dc}} = 2 k T / (e R_s) |(i f / f_s) / (1 + i f / f_s)|^2$$

With the example parameters:  $f_s=160\text{MHz}$

most of the case  $f < f_s$

$$i_{\text{dc}} = 2 k T / (e R_s) * (f / f_s)^2 = 5 (f / 160\text{MHz})^2 \text{ [mA]}$$

$$V_{\text{th}} \sim R_F (f / f_s) * \text{sqrt}[4 k T / R_s] = 40 (f / 160\text{MHz}) \text{ [nV/Hz}^{1/2}\text{]}$$

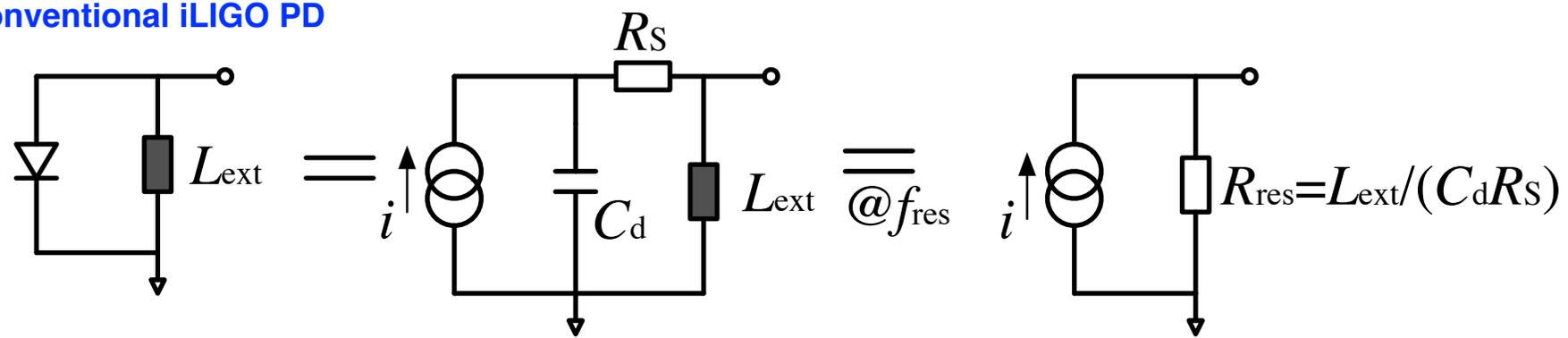
i.e. The noise of  $R_F$  is dominant at  $f < 16\text{MHz}$

Also note that the bandwidth of the PD is limited by  $C_d R_F$

$$f_c = \text{sqrt}[\text{GBW} / (2 \text{ pi } C_d R_F)]$$

e.g.  $\text{GBW}=1\text{GHz}$ ,  $C_d=100\text{pF}$ ,  $R_F=1000 \text{ Ohm} \implies f_c \sim 40\text{MHz}$

C) conventional iLIGO PD



Apparently we can ignore shunt regulator R<sub>SH</sub>

$$V_{\text{shot}} = \sqrt{2 e i_{\text{dc}}} R_{\text{res}}$$

$$V_{\text{th}} = \sqrt{4 k T R_{\text{res}}}$$

$V_{\text{shot}} = V_{\text{th}}$  when

$$i_{\text{dc}} = 2 k T / (e R_{\text{RES}})$$

$$= 2 k T C_d R_s / (e L_{\text{ext}})$$

$$i_{\text{dc}} = 2 k T C_d R_s / (e L_{\text{ext}}) = 2 k T / (e R_s) * (f_{\text{res}}/f_s)^2$$

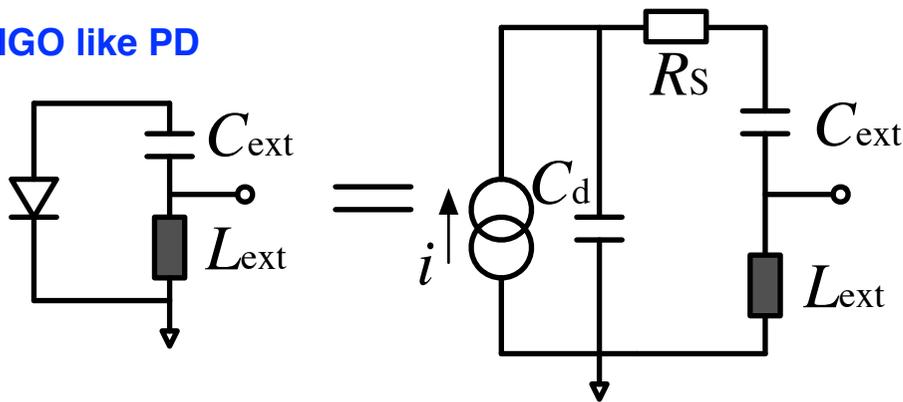
Equivaent to the broadband case!

$$V_{\text{th}} = \sqrt{4 k T R_{\text{res}}} = R_s (f_s/f_{\text{res}}) * \sqrt{4 k T / R_s}$$

Amplifier requirement

resonant vs broadband:  $R_s (f_s/f) > (f/f_s)$  when  $f < 500\text{MHz}$

## D) aLIGO like PD



Again the shunt regulator is ignored.  
 $R_s$  may include the series resistor of the external capacitor.

Resonant condition:  $L_{ext} = (1/C_d + 1/C_{ext}) / (2\pi f_{res})^2$

$$V_{shot} = \sqrt{2 e i_{dc}} R_s (f_s + f_{ext}) f_s / (f_{res})^2$$

$$V_{th} = (f_s + f_{ext}) / f_{res} \sqrt{4 k T R_s} \quad \text{Slightly larger than c)}$$

$$(f_s = 1 / (2\pi R_s C_d), f_{ext} = 1 / (2\pi R_s C_{ext}))$$

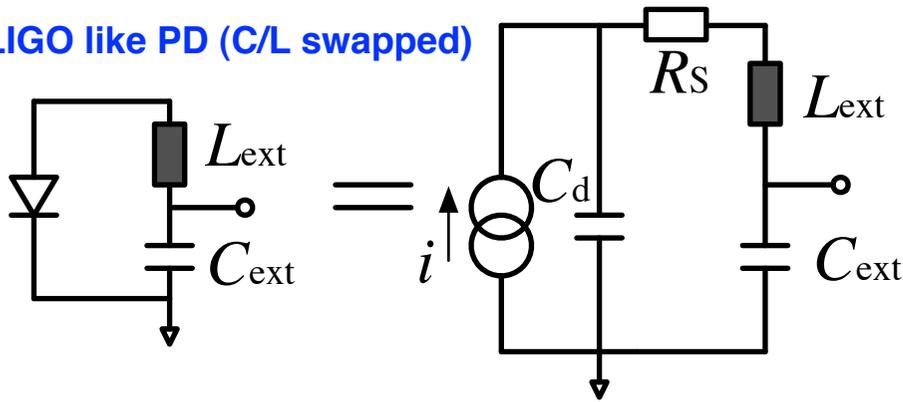
$V_{shot} = V_{th}$  when

$$i_{dc} = 2 k T / (e R_s) * (f_{res} / f_s)^2$$

Equivalent to the iLIGO PD case!

The cut off freqs  $f_s$  and  $f_{ext}$  higher, the amplification of the signal larger  
 (i.e. easier to work with)

D') aLIGO like PD (C/L swapped)



Resonant condition:  $L_{ext} = (1/C_d + 1/C_{ext}) / (2 \pi f_{res})^2$

Same as D)

$V_{shot} = \sqrt{2 e i_{dc}} R_s (f_s f_{ext}) / (f_{res})^2$  Smaller than D)

$V_{th} = (f_s + f_{ext}) / f_{res} \sqrt{4 k T R_s}$  Same as D)

$V_{shot} = V_{th}$  when

$i_{dc} = 2 k T / (e R_s) * (f_{res} / f_s + f_{res} / f_{ext})^2$

Worse than D) case

In general the performance is worse than the case D)

owing to the smaller amplification of the signal